Exhibit R-2, RDT&E Budget Item Justification: PB 2016 Defense Advanced Research Projects Agency

R-1 Program Element (Number/Name)

Appropriation/Budget Activity 0400: Research, Development, Test & Evaluation, Defense-Wide I BA 3:

PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES

Date: February 2015

Advanced Technology Development (ATD)

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COST (\$ in Millions)	Prior Years	FY 2014	FY 2015	FY 2016 Base	FY 2016 OCO	FY 2016 Total	FY 2017	FY 2018	FY 2019	FY 2020	Cost To Complete	Total Cost
Total Program Element	-	92.001	92.246	79.021	-	79.021	87.381	115.033	148.689	169.859	-	-
MT-12: MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY	-	32.632	14.264	-	-	-	-	-	-	-	-	-
MT-15: MIXED TECHNOLOGY INTEGRATION	-	59.369	77.982	79.021	-	79.021	87.381	115.033	148.689	169.859	-	-

A. Mission Description and Budget Item Justification

The Advanced Electronics Technologies program element is budgeted in the Advanced Technology Development Budget Activity because it seeks to design and demonstrate state-of-the-art manufacturing and processing technologies for the production of various electronics and microelectronic devices, sensor systems, actuators and gear drives that have military applications and potential commercial utility. Introduction of advanced product design capability and flexible, scalable manufacturing techniques will enable the commercial sector to rapidly and cost-effectively satisfy military requirements.

The MicroElectroMechanical Systems (MEMS) and Integrated Microsystems Technology project is a broad, cross-disciplinary initiative to merge computation and power generation with sensing and actuation to realize a new technology for both perceiving and controlling weapons systems and battlefield environments. MEMS applies the advantages of miniaturization, multiple components and integrated microelectronics to the design and construction of integrated electromechanical and electro-chemical-mechanical systems to address issues ranging from the scaling of devices and physical forces to new organization and control strategies for distributed, high-density arrays of sensor and actuator elements. The project will also address thermal management, navigation and positioning technology challenges.

The Mixed Technology Integration project funds advanced development and demonstrations of selected basic and applied electronics research programs. Examples of activities funded in this project include, but are not limited to: (1) component programs that integrate mixed signal (analog and digital; photonic and electronic) or mixed substrate (Gallium Nitride, Gallium Arsenide, Indium Phosphide, or Silicon Germanium with CMOS) technology that will substantially improve the capability of existing components and/or reduce size, weight and power requirements to a level compatible with future warfighter requirements; (2) development and demonstration of brassboard system applications in such areas as laser weaponry or precision navigation and timing to address mid-term battlefield enhancements; and (3) novel technological combinations (i.e. photonics, magnetics, frequency attenuators) that could yield substantial improvement over current systems.

Exhibit R-2, RDT&E Budget Item Justification: PB 2016 Defense Advanced Research Projects Agency

Appropriation/Budget Activity

0400: Research, Development, Test & Evaluation, Defense-Wide I BA 3:

R-1 Program Element (Number/Name)

PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES

Date: February 2015

Advanced Technology Development (ATD)

B. Program Change Summary (\$ in Millions)	FY 2014	FY 2015	FY 2016 Base	FY 2016 OCO	FY 2016 Total
Previous President's Budget	107.080	92.246	83.198	-	83.198
Current President's Budget	92.001	92.246	79.021	-	79.021
Total Adjustments	-15.079	-	-4.177	-	-4.177
 Congressional General Reductions 	-	-			
 Congressional Directed Reductions 	-	-			
 Congressional Rescissions 	-	-			
 Congressional Adds 	-	-			
 Congressional Directed Transfers 	-	-			
 Reprogrammings 	-11.913	-			
SBIR/STTR Transfer	-3.166	-			
 TotalOtherAdjustments 	-	-	-4.177	-	-4.177

Change Summary Explanation

FY 2014: Decrease reflects below threshold and omnibus reprogrammings and the SBIR/STTR transfer.

FY 2016: Decrease reflects completion of the MEMS and Integrated Microsystems Technology Project (MT-12).

Exhibit R-2A, RDT&E Project Ju	ustification	: PB 2016 E	Defense Adv	anced Res	search Proje	cts Agency				Date: Feb	ruary 2015	
Appropriation/Budget Activity 0400 / 3						39E <i>I ADVA</i>	•	•	Project (Number/Name) MT-12 / MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY			_
COST (\$ in Millions)	Prior Years	FY 2014	FY 2015	FY 2016 Base	FY 2016 OCO	FY 2016 Total	FY 2017	FY 2018	FY 2019	FY 2020	Cost To Complete	Total Cost
MT-12: MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY	-	32.632	14.264	-	-	-	-	-	-	-	-	-

A. Mission Description and Budget Item Justification

The MicroElectroMechanical Systems (MEMS) and Integrated Microsystems Technology program is a broad, cross-disciplinary initiative to merge computation and power generation with sensing and actuation to realize a new technology for both perceiving and controlling weapons systems and battlefield environments. Using fabrication processes and materials similar to those used to make microelectronic devices, MEMS applies the advantages of miniaturization, multiple components and integrated microelectronics to the design and construction of integrated electromechanical and electro-chemical-mechanical systems. The MEMS program addresses issues ranging from the scaling of devices and physical forces to new organization and control strategies for distributed, high-density arrays of sensor and actuator elements. These issues include microscale power and actuation systems as well as microscale components that survive harsh environments. Thermal management technologies will develop heat resistant thermal layers to provide efficient operation for cooling electronic devices. The current focus in micro technologies is to improve navigation, position and timing capabilities for uncompromised navigation and positioning in today's dynamic military field of operations.

B. Accomplishments/Planned Programs (\$ in Millions)	FY 2014	FY 2015	FY 2016
Title: Micro-Technology for Positioning, Navigation, and Timing (Micro PN&T)	28.259	14.264	-
Description: The Micro-Technology for Positioning, Navigation, and Timing (Micro-PNT) program is developing low-Cost, Size, Weight, and Power (CSWaP) inertial sensors and timing sources for navigation in GPS degraded environments, primarily focusing on the development of miniature solid state and atomic gyroscopes and clocks. Both classes of sensors are currently unsuitable for small platform or dismount soldier applications. Micro Electro-Mechanical Systems (MEMS) sensors have limited performance but excellent CSWaP, while atomic sensors are capable of excellent performance but are limited to laboratory experiments due to complexity and high CSWaP. Micro-PNT is advancing both technology approaches by improving the performance of MEMS inertial sensors and by miniaturizing atomic devices. Ultimately, low-CSWaP inertial sensors and clocks will enable ubiquitous guidance and navigation on all platforms, including guided munitions, unmanned aerial vehicles (micro-UAVs), and mounted and dismounted soldiers. Successful realization of Micro-PNT requires the development of new microfabrication processes and novel material systems for fundamentally different sensing modalities, understanding of the error sources at the microscale, and development of miniature inertial sensors based on atomic physics. Innovative microfabrication techniques under development will allow co-fabrication of dissimilar devices on a single chip, such that clocks, gyroscopes, accelerometers, and calibration stages can be integrated into a small, low power architecture. The program is developing miniature inertial sensors based on atomic interferometry and nuclear magnetic resonance. Ancillary research efforts for this program are funded within PE 0602716E, Project ELT-01.			

PE 0603739E: *ADVANCED ELECTRONICS TECHNOLOGIES* Defense Advanced Research Projects Agency

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Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense A	dvanced Research Projects Agency	Date: F	ebruary 2015		
Appropriation/Budget Activity 0400 / 3	PE 0603739E I ADVANCED	MT-12 I MEMS AND INTEGI			
B. Accomplishments/Planned Programs (\$ in Millions)		FY 2014	FY 2015	FY 2016	
 FY 2014 Accomplishments: Demonstrated basic functionality of miniature atomic physics-ba Demonstrated functionality of MEMS gyro and co-fabricated cali Demonstrated integration of atomic interferometry inertial sensor Demonstrated miniaturized trapped ion clock, with roadmap to s Demonstrated electronic gyroscope self-calibration with long-term Demonstrated personal navigation for 4-hour long test with tight 	bration stage. r with high-bandwidth co-sensor. elf-contained, portable operation. m scale factor and bias of <10 ppm of full range.				
 FY 2015 Plans: Demonstrate a miniature, self-contained atomic gyroscope with a stability < 0.01 degrees/hr. Demonstrate self-calibrating MEMS gyroscope with long-term self-calibrating memory. 		as			
Title: Blast Exposure Accelerated Sensor Transfer (BEAST)		4.373	-		
Description: The Blast Exposure Accelerated Sensor Transition (Gauge program and enabled a better understanding of blast-related Traumatic Stress Disorder (PTSD). During a blast event, the Blast operational information in order to develop a 3D recreation of the emilitary community, conducted cognitive testing in high risk services impact of blast exposure by correlating physiological and behavior these results contributed to the TBI and PTSD knowledge base for blast events to mitigate exposure and improved training procedure device to military service sustainment.	ed injuries such as Traumatic Brain Injury (TBI) and Post- t Gauge device captures environmental data and available event. The BEAST program provided additional tools for the emembers, and expanded the current knowledge base of the al changes with direct measures of blast-exposure. Ultimate improved treatment, developed enhanced understanding of	e ne rely, of			
 FY 2014 Accomplishments: Supported medical studies using Blast Gauge devices. Completed development of a web-based tool to store, organize, Issued 5th generation Blast Gauge devices to groups of Service Concluded verification and validation blast testing event with Arr Finalized approvals to commence clinical studies on physiologic Established data collection plan for cognitive testing in clinical page 	members. ny Testing Center at Aberdeen Proving Grounds. al and behavioral measures correlated to blast exposure.				
	Accomplishments/Planned Programs Subt	otals 32.632	14.264		

Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense Advanced Res	search Projects Agency	Date: February 2015
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E / ADVANCED ELECTRONICS TECHNOLOGIES	Project (Number/Name) MT-12 I MEMS AND INTEGRATED MICROSYSTEMS TECHNOLOGY
C. Other Program Funding Summary (\$ in Millions)		
N/A		
<u>Remarks</u>		
D. Acquisition Strategy N/A		
E. Performance Metrics		
Specific programmatic performance metrics are listed above in the program ac	ccomplishments and plans section.	

Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense Advanced Research Projects Agency						Date: Febr	uary 2015					
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E / ADVANCED MT-15 / MIXED TECHNOLOGIES INTEGRATION				,							
COST (\$ in Millions)	Prior Years	FY 2014	FY 2015	FY 2016 Base	FY 2016 OCO	FY 2016 Total	FY 2017	FY 2018	FY 2019	FY 2020	Cost To Complete	Total Cost
MT-15: MIXED TECHNOLOGY INTEGRATION	-	59.369	77.982	79.021	-	79.021	87.381	115.033	148.689	169.859	-	-

A. Mission Description and Budget Item Justification

R Accomplishments/Planned Programs (\$ in Millions)

The Mixed Technology Integration project funds advanced development and demonstrations of selected basic and applied electronics research programs. Examples of activities funded in this project include, but are not limited to: (1) component programs that integrate mixed signal (analog and digital; photonic and electronic) or mixed substrate (Gallium Nitride, Gallium Arsenide, Indium Phosphide, or Silicon Germanium with CMOS) technology that will substantially improve the capability of existing components and/or reduce size, weight and power requirements to a level compatible with future warfighter requirements; (2) development and demonstration of brassboard system applications in such areas as laser weaponry or precision navigation and timing to address mid-term battlefield enhancements; and (3) novel technological combinations (i.e. photonics, magnetics, frequency attenuators) that could yield substantial improvement over current systems.

B. Accomplishments/Planned Programs (\$ in Millions)	FY 2014	FY 2015	FY 2016
Title: Endurance	17.859	37.669	23.473
Description: The Endurance program will develop technology for pod-mounted lasers to protect a variety of airborne platforms from emerging and legacy electro-optical IR guided surface-to-air missiles. The focus of the Endurance effort will be to develop and test ancillary subsystems, such as a command subsystem, a threat missile warning subsystem, a mechanical support framework, subsystem interfaces, and the design, integration, and testing of a form/fit/function brass-board laser countermeasure. This program is an early application of technology developed in the Excalibur program and will transition via industry. Applied research for this program is budgeted in PE 0602702E, project TT-06.			
 FY 2014 Accomplishments: Developed critical design of ancillary subsystems (power supply, thermal management, processing and control, mechanical support framework). Developed preliminary design for subsystem integration including optical and electrical interconnections and their layouts. 			
 FY 2015 Plans: Acquire threat devices and/or surrogates in preparation for live fire testing. Complete the critical design for subsystem integration. Integrate, assemble and bench-test the brassboard system. 			
FY 2016 Plans: - Test the brassboard laser weapon system at an outdoor test range against a representative set of dynamic-threat targets. - Assess brassboard system performance in live-fire testing.			

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Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense A	Advanced Research Projects Agency	Date:	ebruary 2015	j	
Appropriation/Budget Activity 0400 / 3	Ctivity R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES				
B. Accomplishments/Planned Programs (\$ in Millions)		FY 2014	FY 2015	FY 2016	
- Develop a preliminary engineering design for a flight-prototype	of a pod-mounted laser weapon system.				
Title: Diverse & Accessible Heterogeneous Integration (DAHI)		13.910	20.300	12.75	
Description: Prior DARPA efforts have demonstrated the ability of achieve near-ideal "mix-and-match" capability for DoD circuit des Semiconductor Materials On Silicon (COSMOS) program, in which with silicon complementary metal-oxide semiconductor (CMOS) of speed and very high circuit complexity/density, respectively). The will take this capability to the next level, ultimately offering the sea example, Gallium Nitride (GaN), InP, Gallium Arsenide, Antimonic (MEMS) sensors and actuators, photonic devices (e.g., lasers, photonic devices) in a capability will revolutionize our ability to build true "systems on a control of the capability will revolutionize our system applications.	igners. Specifically, one such program was the Compound the transistors of Indium Phosphide (InP) could be freely mix circuits to obtain the benefits of both technologies (very high e Diverse & Accessible Heterogeneous Integration (DAHI) amless co-integration of a variety of semiconductor devices de Based Compound Semiconductors), microelectromechanoto-detectors) and thermal management structures. This	ed o effort (for			
This program has basic research efforts funded in PE 0601101E, 0602716E, Project ELT-01. The Advanced Technology Developmefforts to focus on the establishment of an accessible, manufactural a wide array of materials and devices (including, for example, mure enabled (e.g. CMOS) architectures on a common silicon substrate accessible foundry processes of DAHI technology and demonstrate and designs that leverage heterogeneous integration. By the encompanion of DoD laboratory, Federally Funded Research and Development	ment part of this program will leverage these complementar rable technology for device-level heterogeneous integration altiple electronics and MEMS technologies) with complex sile platform. This part of the program is expected to culminations of advanced microsystems with innovative architecture of the program, this effort seeks to establish a technologic with appropriate computer-aided design support) to a wide	n of icon- ite in res ally			
FY 2014 Accomplishments: - Developed a high-yield, high-reliability accessible manufacturin foundry activity providing heterogeneously integrated circuits with Heterojunction Bipolar Transistor (HBTs), GaN High-electron-mole. - Developed three-technology chiplet-based heterogeneous integration run. - Developed process for integration of third-party device technologies. - Established heterogeneous integration design/simulation tool flomicrosystems integration. - Developed thermal simulation tools and process design kit for high the simulation tools and process design kit for high the simulation tools and process design kit for high the simulation tools are simulation tools.	n four materials/device technologies (Silicon (Si) CMOS, InFibility transistor (HEMTs), and high-Q passive devices). gration process for use in initial heterogeneous integration regies in heterogeneous integration foundry. ows necessary to realize the full potential of heterogeneous	multi-			

Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense A	dvanced Research Projects Agency		Date: Fe	ebruary 2015	
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	Project (Number/Name) MT-15 / MIXED TECHNOLOGY INTEGRATION			
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2014	FY 2015	FY 2016
 Demonstrated capability for supporting multi-project wafer runs of the contract o	n for initial heterogeneous integration foundry run. odologies that enable revolutionary heterogeneously integra	ated			
FY 2015 Plans: - Continue to develop a high-yield, high-reliability accessible manusustaining foundry activity providing heterogeneously integrated ci HBTs, GaN HEMTs, and high-Q passive devices). - Continue to demonstrate capability for supporting multi-project widevelopment.	rcuits with four materials/device technologies (Si CMOS, Ir	nΡ			
FY 2016 Plans: - Complete development of a high-yield, high-reliability accessible sustaining foundry activity providing heterogeneously integrated ci HBTs, GaN HEMTs, and high-Q passive devices). - Complete demonstration of capability for supporting multi-project development.	rcuits with four materials/device technologies (Si CMOS, Ir	ıΡ			
Title: FLASH - Scaling Fiber Arrays at Near Perfect Beam Quality			11.600	18.013	14.100
Description: The goal of the FLASH program is to demonstrate a from coherently combining the outputs of an array of ultra-lightweig laser system will project a >30-kW-class beam with near perfect be size, weight, and power (SWaP) will be consistent with weight and weapons on a broad range of Military platforms. To accomplish the weight of packaged coherently-combinable high-power fiber laser support systems such as cabling, cooling lines and support structure vibration and acoustics and (2) fabricate an array of these ultralight power, thermal management and coherent-beam combination substantial process.	ght, flight-worthy high power fiber lasers. The packaged FL eam quality and very high electrical-to-optical efficiency. To volume densities needed to support the integration of lase lese ends, FLASH will (1) greatly reduce the overall size an amplifiers while greatly simplifying the demands they make lares while increasing their efficiency and resistance to shoot of the fiber-laser amplifiers and integrate them with advanced but	ASH he or od on ck, attery			
FY 2014 Accomplishments: - Demonstrated a benchtop array of 1.3 kW fiber-lasers combined electrical-to-optical efficiency.	I to produce a >30 kW near-diffraction-limited output at >25	5%			

PE 0603739E: ADVANCED ELECTRONICS TECHNOLOGIES UNCLASSIFIED

Defense Advanced Research Projects Agency

Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense Ad	vanced Research Projects Agency	Date	: February 2015	,	
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES		oject (Number/Name) T-15 I MIXED TECHNOLOGY TEGRATION		
B. Accomplishments/Planned Programs (\$ in Millions)		FY 2014	FY 2015	FY 2016	
 Estimated the capability of a 21-element optical-phased array sysatmospheric conditions. Demonstrated target-in-the-loop phase-locking on a stationary tar 	·	rious			
FY 2015 Plans: - Develop and test a packaged, flight-worthy, coherently-combinab and weight consistent with system integration on tactical aircraft. - Develop a preliminary design for a >30 kW, transportable, package power systems, and beam combination.					
FY 2016 Plans: - Develop a critical design for a >30 kW transportable, packaged la - Fabricate and /or procure parts and hardware for the >30 kW, transportable - Assemble and test key subsystems for the >30 kW, transportable - Begin the integration of key subsystems for a >30 kW, transporta	nsportable, packaged laser system. , packaged laser system.				
Title: Direct SAMpling Digital ReceivER (DISARMER)		2.00	2.000	2.00	
Description: The goal of the Direct SAMpling Digital ReceivER (DI analog-to-digital converter (ADC) capable of coherently sampling the electronic wideband receivers are limited in dynamic range by both an ultra-stable optical clock, the DISARMER program will allow for a 100x over the state of the art. Such a wide-bandwidth, high-fidelity intelligence systems with the potential to drastically reduce the cost	the entire X-band (8-12 GigaHertz (GHz)). Conventional the electronic mixer and the back-end digitizers. By emprixer-less digitization and thereby improve the dynamic receiver will have applications in electronic warfare and	oloying ange			
The DISARMER program will design, fabricate, and test a hybrid phenic involves the integration of electronic and photonic circuits, pact delivering a field programmable gate array with the necessary firmwaresearch efforts funded in PE 0602716E, Project ELT-01.	kaging of a mode-locked laser with ultralow jitter, and				
FY 2014 Accomplishments: - Defined system architecture and flow-down metrics for individual - Designed and fabricated a novel, single channel optical receiver of the components to incomply the components to incompliance.	chip capable of receiving electrical pulses that are < 2 ps				
FY 2015 Plans:					

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Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense	Advanced Research Projects Agency		Date: F	ebruary 2015	5	
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	Project MT-15 / INTEGR	Name) ECHNOLOGY	3Y		
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2014	FY 2015	FY 2016	
 Design, fabricate and test the second generation optical receive minimize the parasitic capacitance of the circuit. Complete system engineering of field programmable gate array. Demonstrate direct sampling of a 2 GHz-wide bandwidth signal. 	y capable of continuous streaming of digital data.					
FY 2016 Plans: - Demonstrate direct sampling of a 4 GHz-wide bandwidth signal	al at 10 effective bits of fidelity.					
Title: Photonic Radio			-	-	9.89	
Description: The rapid pace of wireless technology development components that span the radio spectrum up to 100 GHz. When bandwidth, conventional radio frequency (RF) systems perform proceedings of the description of the process	a faced with agile or unknown threats across decades of poorly. Massively channelized receivers spanning just tens large defense platforms. Recent developments in integrate and down-convert RF signals in the photonic domain with the Photonic Radio program will build on this foundation to determine the program will design and controlled with high performance photonic devices, such as very	of ed eliver d build ery				
FY 2016 Plans:Design and simulate the complete channelized receiver and geFabricate and test integrated photonic down-converter and high		S.				
Title: Fast and Big Mixed-Signal Designs (FAB)			-	-	7.20	
Description: Developing capabilities to intermix and tightly integ scaling nodes and by different vendors is critical to increasing the example, Silicon-Germanium (SiGe) Bipolar Complementary Met logic to be integrated with radio frequency (RF) heterojunction bip having RF analog capabilities tightly coupled to digital processing to a single CMOS technology node and significant design and en Thus, BiCMOS processes tend to lag behind commercial CMOS potential for a truly process-agnostic integration technology, i.e. of technology such as Gallium Arsenide (GaAs), Gallium Nitride (Gaat technology platform will enable the design of individual circuit lines.	e capabilities of high-performance military microelectronics. tal-oxide Semiconductor (BiCMOS) processes allow CMOS polar transistors (HBTs), which enables mixed-signal circuitg. However, the SiGe process flow was developed to integngineering effort is required to retarget the flow for a new not by several generations. This program will investigate the one that is inclusive of any current or future circuit fabricationally and SiGe with a standardized interconnect topology.	For S ts rate ode.				

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Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense A	dvanced Research Projects Agency		Date: F	ebruary 2015	5
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	MT-15	Project (Number/Name) MT-15 / MIXED TECHNOLOGY INTEGRATION		
B. Accomplishments/Planned Programs (\$ in Millions)		Γ	FY 2014	FY 2015	FY 2016
analog-to-digital converters, with a goal of re-use of the IP across design cost of these blocks over several designs instead of levelin designed in the fabrication process best suited for the performance single chip systems-on-a-chip. Through standardization of the integriven by the global semiconductor market rather than relying on a designs owned by a handful of traditional prime performers.	ng the burden on a single program. Furthermore, the IP ca e goals and evolve more quickly than larger, more expens erface, FAB will enable the DoD to leverage the advancer	an be sive nents			
In the Advanced Technology Development part of this program, for and insertion of microsystems utilizing III-V semiconductors and or program has Applied Research efforts funded in PE 0602716E, Pr	ther microelectronic technologies with advanced Si CMOS				
 FY 2016 Plans: Investigate analog intellectual property (IP) reuse techniques for circuits. Develop standardized, high-bandwidth interfaces for chiplet-to-c Initiate circuit demonstration using intellectual property reuse techniques 	chip interconnection.	wave			
Title: Precise Robust Inertial Guidance for Munitions (PRIGM)	·		-	-	6.28
Description: The Precise Robust Inertial Guidance for Munitions Power (CSWaP) inertial sensor technology for GPS-free munitions of a Navigation-Grade Inertial Measurement Unit (NGIMU) that tra 2) Research and development of Advanced Inertial MEMS Sensor range navigation requirements with the objective of complete auto	s guidance. PRIGM comprises two focus areas: 1) Developments by 2020 rs (AIMS) to achieve gun-hard, high-bandwidth, high dyna	opment ; and			
At present, DoD suffers a trade-space dichotomy between low-CS and relatively high-CSWaP navigation-grade IMUs, based on ring-RLG/iFOG is the technology of choice for high-value platforms. H UAVs), CSWaP necessitates the use of lower-performance MEMS developed MEMS gyroscopes with performance rivaling that of na exposing a new tradespace for low-CSWaP navigation grade IMU level (TRL) of state-of-the-art MEMS inertial sensors from TRL-3 complete MEMS-based navigation-grade IMU with an identical me grade MEMS IMUs, thereby providing a drop-in replacement for extra program has applied research efforts funded in PE 0602716E	-laser or interferometric fiber-optic gyroscopes (RLG/iFOG owever, for the vast majority of platforms (munitions, dismontant of the vast majority of platforms (munitions, dismontant of the program, DARPA havigation-grade interferometric fiber optic gyros (IFOGs), the second of the program is to develop echanical/electronic interface to existing DoD-standard tack xisting DoD systems and rapid transition to TRL-7.	as nounts, as nus liness			

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Exhibit R-2A, RDT&E Project Justification: PB 2016 Defense Advanced Research Projects Agency			Date: February 2015			
Appropriation/Budget Activity 0400 / 3	R-1 Program Element (Number/Name) PE 0603739E I ADVANCED ELECTRONICS TECHNOLOGIES	MT-15	Project (Number/Name) MT-15 / MIXED TECHNOLOGY INTEGRATION			
B. Accomplishments/Planned Programs (\$ in Millions)			FY 2014	FY 2015	FY 2016	
FY 2016 Plans: - Initiate efforts to demonstrate MEMS inertial sensors that meet a requirements - Design, fabricate, and characterize gyroscopes with Angle Rand repeatability of 0.001 deg/hr, in-run bias stability of 0.001 deg/hr, a - Design, fabricate, and characterize accelerometers with Velocity bias repeatability of 25 micro-g, in-run bias stability of 10 micro-g,	dom Walk (ARW) of 0.0035 deg/rt(hour), turn-on-to-turn-o and scale factor repeatability of 5 ppm. A Random Walk (VRW) of 1 mm/sec/rt(hour), turn-on-to-tu	n bias				
Title: Microwaves and Magnetics (M&M)			-	-	3.31	
Description: Passive magnetic components such as frequency sefilters are integral to numerous military electronic systems in applic warfare. However, the rate of development and level of integration severely lagged the corresponding advancements and monolithic (MEMS), and optical active devices. In some cases the magnetic Microwaves and Magnetics program will leverage advanced magnetic performance and novel functionality.	cations including radar, imaging, communications, and elements in microwave and mm-wave magnetic components have integration of semiconductor, microelectromechanical systechnologies have changed little in the past 20 to 30 year	ectronic e stems rs. The				
A particularly attractive magnetic component for front-end receiver high power signals above a certain threshold while allowing low power enable receivers to operate in the presence of strong interferers prenvironments, and increase effective dynamic range. Correspond will dramatically improve the performance, and increase the integral Defense (DoD) applications. This program has applied research enables.	ower signals at different frequencies to pass. Use of FSLs roviding wideband protection, enable operation in conges ling advances in other magnetic components and technoloation level of transmitters and receivers for Department o	s will ted RF ogies				
FY 2016 Plans: - Leverage advances in magnetic materials and microwave design low insertion loss, wide bandwidth, improved transient response, a - Explore potential opportunities for system integration and development	and high power handling capability.					
Title: Low Cost Thermal Imager - Manufacturing (LCTI-M)			14.000	-	-	
Description: The Low Cost Thermal Imager - Manufacturing (LCT and developed a pocket-sized and smartphone-integrated, manufa allows it to be provided to large numbers of warfighters. Availability facilitates new techniques and applications that could provide the or	acturable, and practical thermal imager at a price point that ty of very low cost and small form-factor infrared (IR) cam	at ieras				

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Appropriation/Budget Activity 0400 / 3	,		umber/Name) XED TECHNOLOGY TION

B. Accomplishments/Planned Programs (\$ in Millions)	FY 2014	FY 2015	FY 2016
allow a soldier to have practical thermal imaging capability for locating warm objects (e.g., enemy combatants) in darkness. The small size, weight and power (SWaP) thermal camera can be integrated with a handheld device such as a cell phone with network capability for tactical intelligence, surveillance and reconnaissance. The imager chips were fully integrated with a low-cost processor and optics. The camera has wireless connectivity to integrate video display with cell phones or PDAs. U.S. Army PEO Soldier Sensors and Lasers (SSL), PM Optics USMC, USSOCOM and industry are the transition partners.			
FY 2014 Accomplishments: - Completed low-cost wafer-scale optics for LCTI-M camera. - Demonstrated small-form-factor camera integration employing 3-D assembly techniques. - Delivered interim prototype cameras for testing. - Delivered final 640x480 LCTI-M cameras with test results and 1280X1024 camera engines.			
Accomplishments/Planned Programs Subtotals	59.369	77.982	79.021

C. Other Program Funding Summary (\$ in Millions)

N/A

Remarks

D. Acquisition Strategy

N/A

E. Performance Metrics

Specific programmatic performance metrics are listed above in the program accomplishments and plans section.

PE 0603739E: ADVANCED ELECTRONICS TECHNOLOGIES

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